

INCHANGE Semiconductor

isc Product Specification

isc Silicon PNP Power Transistors

BDT82F/84F/86F/88F

DESCRIPTION

- DC Current Gain  $-h_{FE} = 40(\text{Min}) @ I_C = -5\text{A}$
- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(\text{SUS})} = -60\text{V}(\text{Min})$ - BDT82F;  $-80\text{V}(\text{Min})$ - BDT84F;  
 $-100\text{V}(\text{Min})$ - BDT86F;  $-120\text{V}(\text{Min})$ - BDT88F
- Complement to Type BDT81F/83F/85F/87F

APPLICATIONS

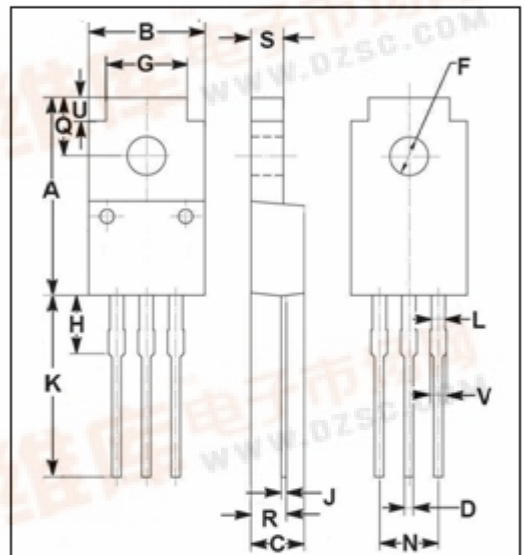
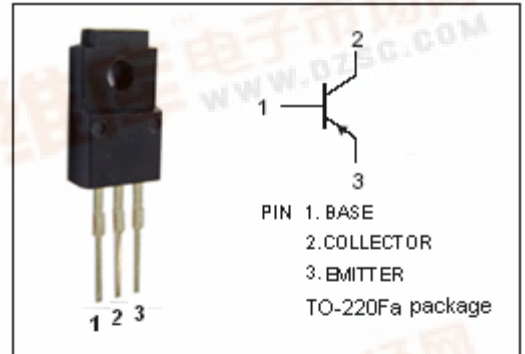
- Designed for use in audio output stages and general amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT	
$V_{CBO}$	Collector-Base Voltage	BDT82F	-60	V
		BDT84F	-80	
		BDT86F	-100	
		BDT88F	-120	
$V_{CEO}$	Collector-Emitter Voltage	BDT82F	-60	V
		BDT84F	-80	
		BDT86F	-100	
		BDT88F	-120	
$V_{EBO}$	Emitter-Base Voltage	-7	V	
$I_C$	Collector Current-Continuous	-15	A	
$I_{CM}$	Collector Current-Peak	-20	A	
$I_B$	Base Current	-4	A	
$P_C$	Collector Power Dissipation $T_C=25^\circ\text{C}$	36	W	
$T_j$	Junction Temperature	150	$^\circ\text{C}$	
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	6	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	16.85	17.15
B	9.90	10.10
C	4.35	4.65
D	0.75	0.80
F	3.20	3.40
G	6.90	7.10
H	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.95	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50



## isc Silicon PNP Power Transistors

## BDT82F/84F/86F/88F

## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(SUS)}$	Collector-Emitter Sustaining Voltage	BDT82F	$I_C = -30\text{mA}; I_B = 0$			V
		BDT84F		-60		
		BDT86F		-80		
		BDT88F		-100		
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -0.5\text{A}$			-1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -7\text{A}; I_B = -0.7\text{A}$			-1.6	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -5\text{A}; V_{CE} = -4\text{V}$			-1.5	V
$I_{CES}$	Collector Cutoff Current	$V_{CE} = 0.8V_{CB0max}; V_{BE} = 0$			-1	mA
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = V_{CB0max}; I_E = 0$			-0.2	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -7\text{V}; I_C = 0$			-0.1	mA
$h_{FE-1}$	DC Current Gain	$I_C = -50\text{mA}; V_{CE} = -10\text{V}$	40			
$h_{FE-2}$	DC Current Gain	$I_C = -5\text{A}; V_{CE} = -4\text{V}$	40			
$f_T$	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -10\text{V}$		20		MHz

## Switching Times

$t_{on}$	Turn-On Time	$I_C = -7\text{A}; I_{B1} = -I_{B2} = -0.7\text{A}$			1	$\mu\text{s}$
$t_{off}$	Turn-Off Time				2	$\mu\text{s}$